

60V N-Channel MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
60V	2.3m Ω @10V	125A

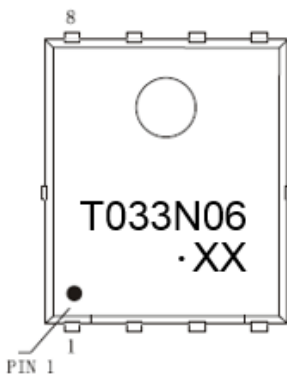
Feature

- Shielded Gate Trench Technology
- Low $R_{DS(on)}$
- Low Gate Charge
- AEC-Q101 qualified (Automotive grade with suffix "Q".)

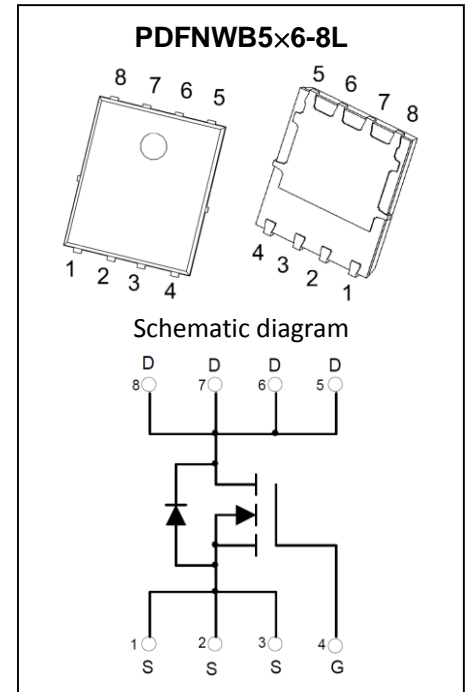
Application

- High efficiency power supply
- Secondary synchronus rectifier

MARKING:



T033N06 = Device code
 XX = Date Code
 Solid dot = Green Device

ABSOLUTE MAXIMUM RATINGS ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	125	A
Pulsed Drain Current	I_{DM}	600	A
Power Dissipation	P_D	3.1	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	40.3	$^{\circ}\text{C}/\text{W}$
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55~+150	$^{\circ}\text{C}$

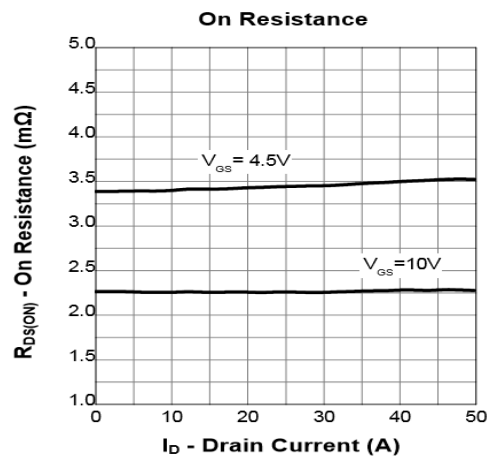
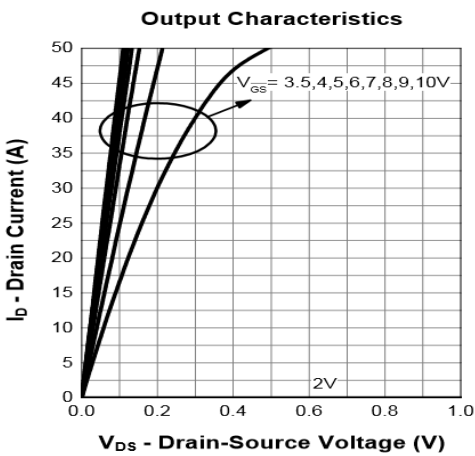
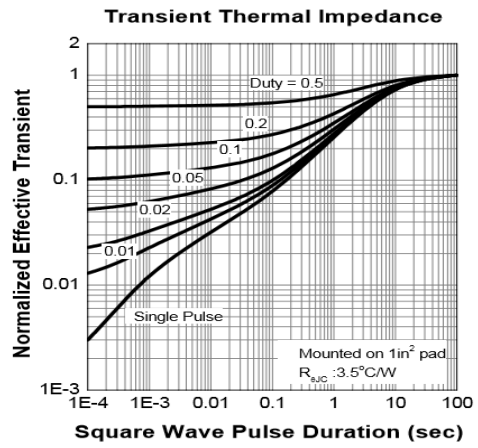
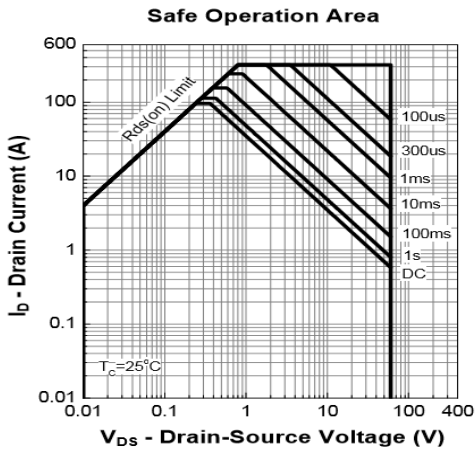
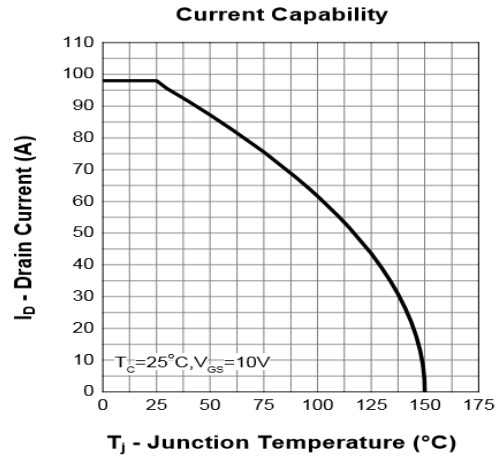
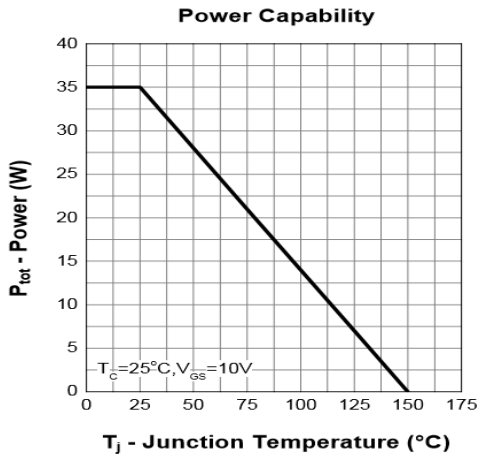
MOSFET ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	60			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 48V, V_{GS} = 0V$			1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
Gate threshold voltage ¹	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.0	2.0	3.0	V
Drain-source on-resistance ¹	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 20A$		2.3	3.3	$m\Omega$
		$V_{GS} = 4.5V, I_D = 20A$		3.5	4.6	$m\Omega$
Dynamic characteristics²						
Input capacitance	C_{iss}	$V_{DS} = 30V, V_{GS} = 0V, f = 1MHz$		4895		pF
Output capacitance	C_{oss}			2208		
Reverse transfer capacitance	C_{rss}			171		
Switching Characteristics²						
Total gate charge	Q_g	$V_{DS} = 30V, V_{GS} = 10V, I_D = 25A$		99		nC
Gate-source charge	Q_{gs}			16		
Gate-drain charge	Q_{gd}			27		
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 30V, R_L = 1.2\Omega, I_D = 25A,$ $V_{GEN} = 10V, R_g = 4.5\Omega$		14		ns
Turn-on rise time	t_r			36		
Turn-off delay time	$t_{d(off)}$			75		
Turn-off fall time	t_f			50		
Diode Characteristics						
Diode Forward Voltage ¹	V_{SD}	$V_{GS} = 0V, I_S = 25A$			1.02	V

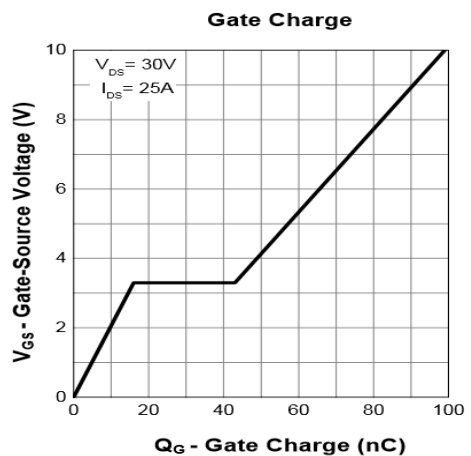
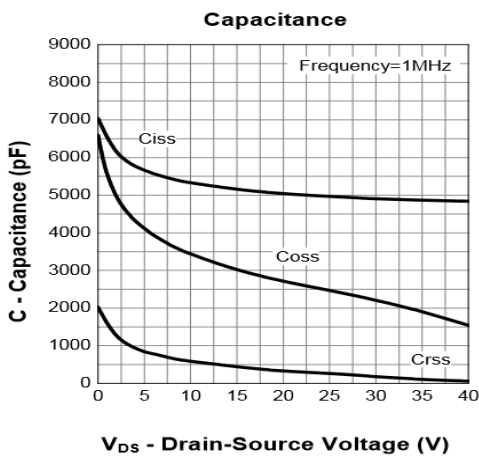
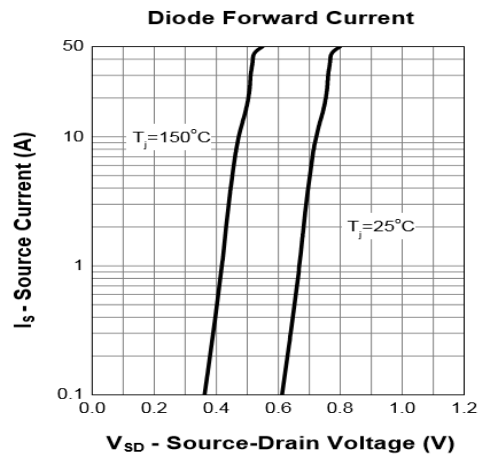
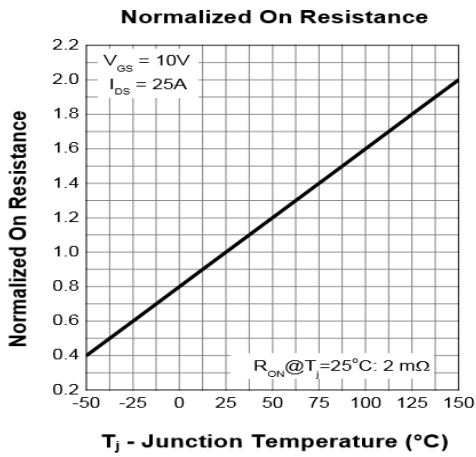
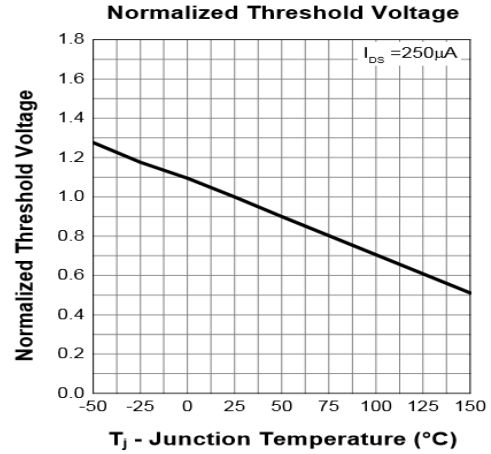
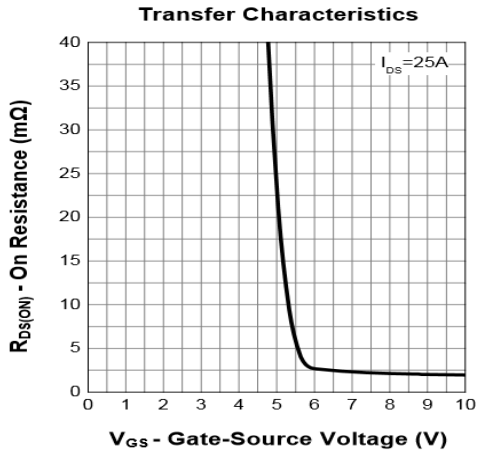
Notes:

1. Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
2. Guaranteed by design, not subject to production testing.

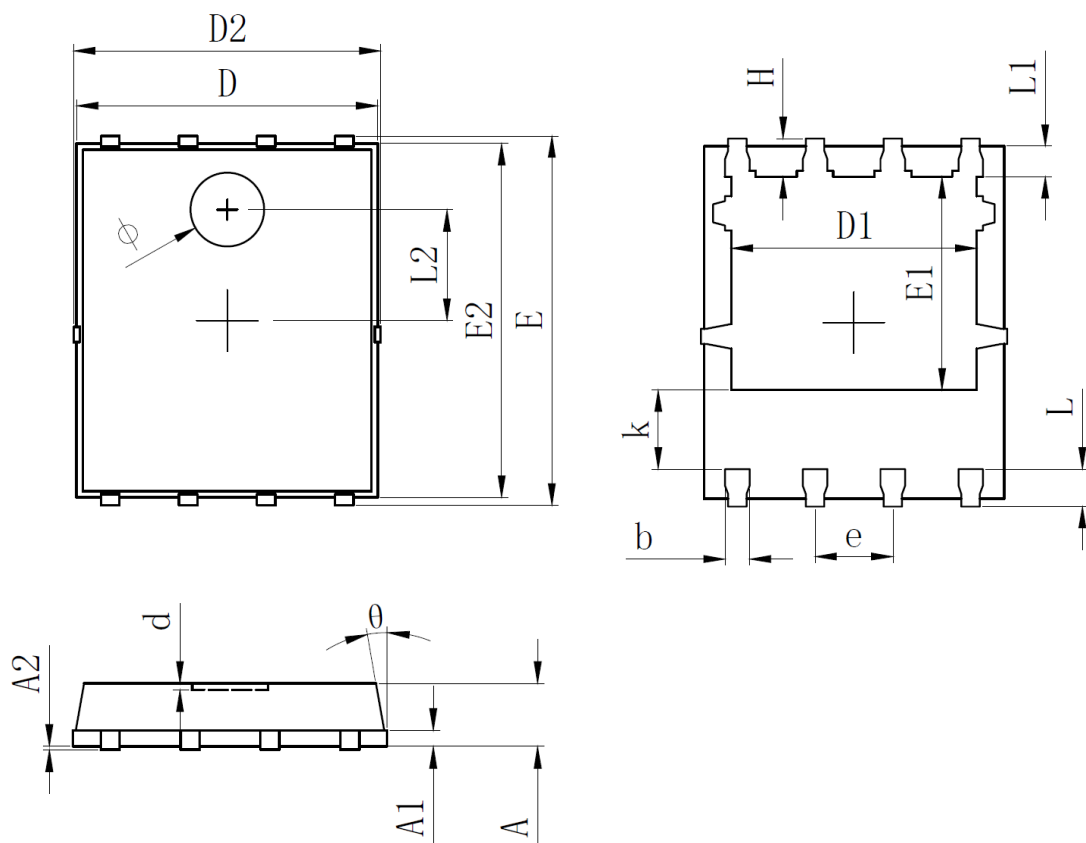
Typical Electrical and Thermal Characteristics



Typical Electrical and Thermal Characteristics



PDFNWB5x6-8L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043
A1	0.254REF		0.010REF	
A2	0.000	0.050	0.000	0.002
D	4.824	4.976	0.190	0.196
D1	3.910	4.110	0.154	0.162
D2	4.924	5.076	0.194	0.200
E	5.924	6.076	0.233	0.239
E1	3.375	3.575	0.133	0.141
E2	5.674	5.826	0.223	0.229
b	0.350	0.450	0.014	0.018
e	1.270TYP		0.050TYP	
L	0.534	0.686	0.021	0.027
L1	0.424	0.576	0.017	0.023
k	1.190	1.390	0.047	0.055
H	0.549	0.701	0.022	0.028
θ	8°	12°	8°	12°
Φ	1.100	1.300	0.043	0.051
d	-	0.100	-	0.004